



SPN4920A

N-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPN4920A is the Dual N-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application , notebook computer power management and other battery powered circuits where high-side switching .

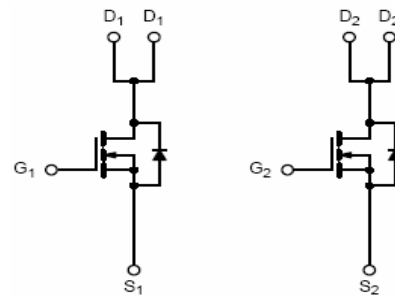
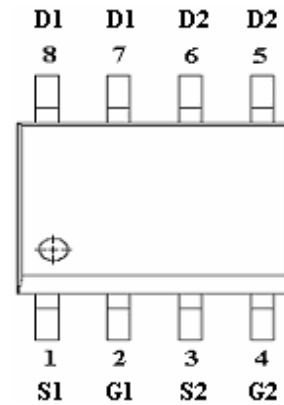
FEATURES

- ◆ 30V/6.8A, $R_{DS(ON)} = 35m\Omega @ V_{GS} = 10V$
- ◆ 30V/5.8A, $R_{DS(ON)} = 45m\Omega @ V_{GS} = 4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOP – 8P package design

APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOP – 8P)



PART MARKING



A : Lot Code
B : Date Code



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PIN DESCRIPTION

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	S2	Source 2
4	G2	Gate 2
5	D2	Drain 2
6	D2	Drain 2
7	D1	Drain 1
8	D1	Drain 1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN4920AS8RG	SOP- 8P	SPN4920A
SPN4920AS8TG	SOP- 8P	SPN4920A

※ SPN4920AS8RG : 13" Tape Reel ; Pb – Free

※ SPN4920AS8TG : Tube ; Pb – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	30	V
Gate –Source Voltage	V _{GSS}	±20	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	6.8
		TA=70°C	5.8
Pulsed Drain Current	I _{DM}	35	A
Continuous Source Current(Diode Conduction)	I _S	1.7	A
Power Dissipation	P _D	TA=25°C	2.8
		TA=70°C	1.8
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	65	°C/W



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ELECTRICAL CHARACTERISTICS

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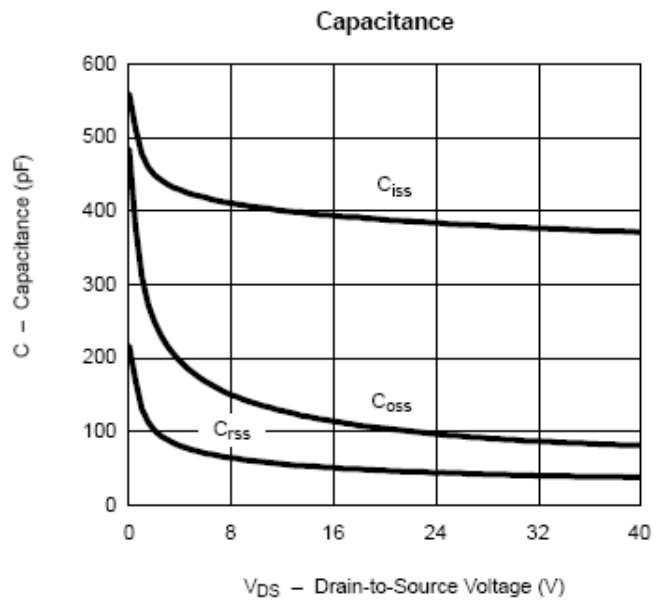
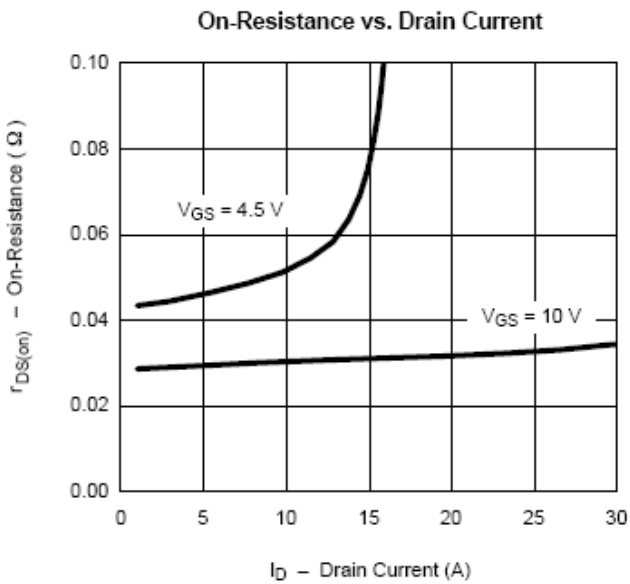
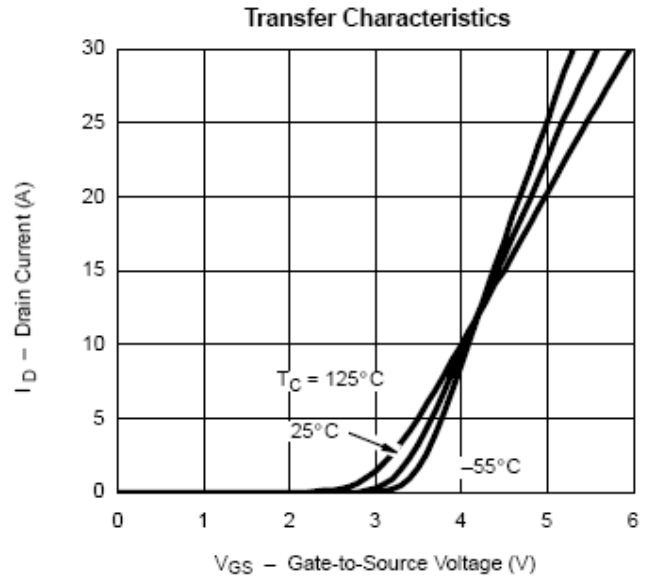
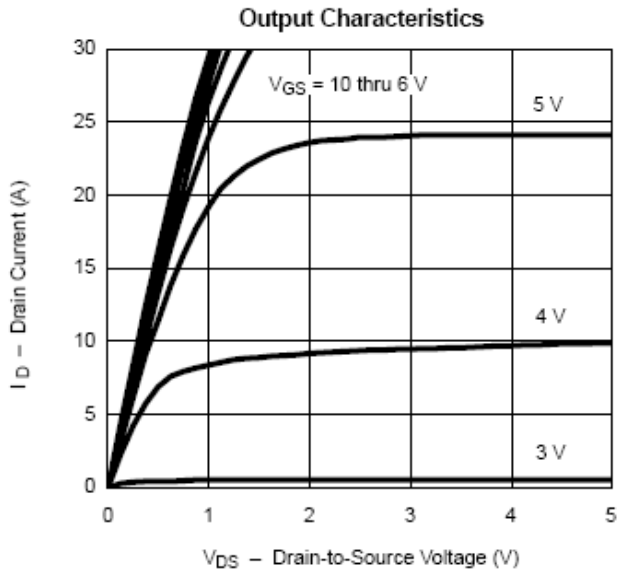
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		3.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	uA
		$V_{DS}=30V, V_{GS}=0V$ $T_J=85^\circ C$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS} = 10V$	20			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 6.8A$		0.026	0.035	Ω
		$V_{GS} = 4.5V, I_D = 5.8A$		0.036	0.045	
Forward Transconductance	g_{fs}	$V_{DS} = 15V, I_D = 6.2A$		13		S
Diode Forward Voltage	V_{SD}	$I_S = 2.0A, V_{GS} = 0V$		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 20V, V_{GS} = 10V$ $I_D = 7.2A$		10	15	nC
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			2.3		
Turn-On Time	$t_{d(on)}$	$V_{DD} = 20V, R_L = 20\Omega$ $I_D = 1.0A, V_{GEN} = 10V$ $R_G = 6\Omega$		8	15	nS
	t_r			12	25	
Turn-Off Time	$t_{d(off)}$			15	35	
	t_f			10	20	



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TYPICAL CHARACTERISTICS

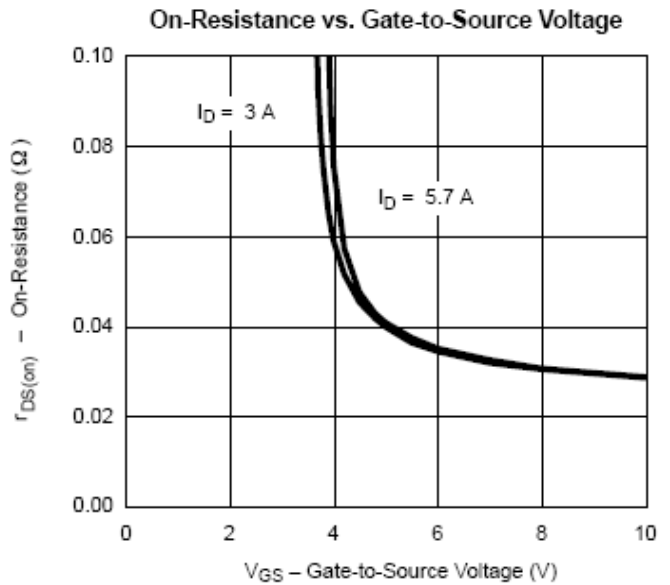
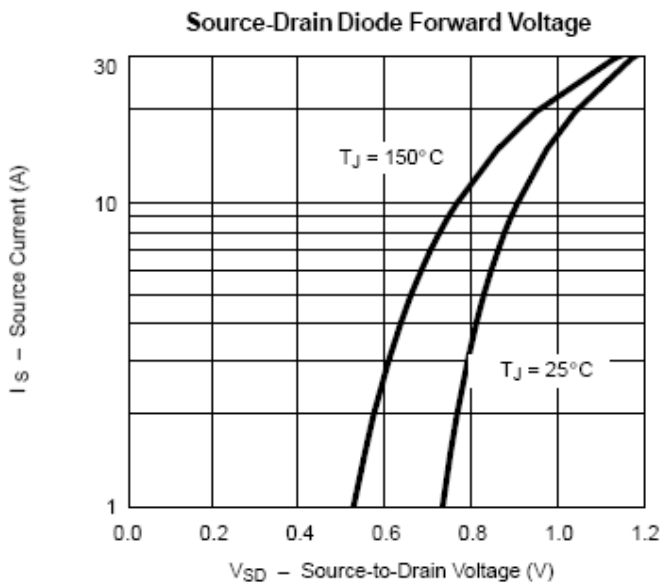
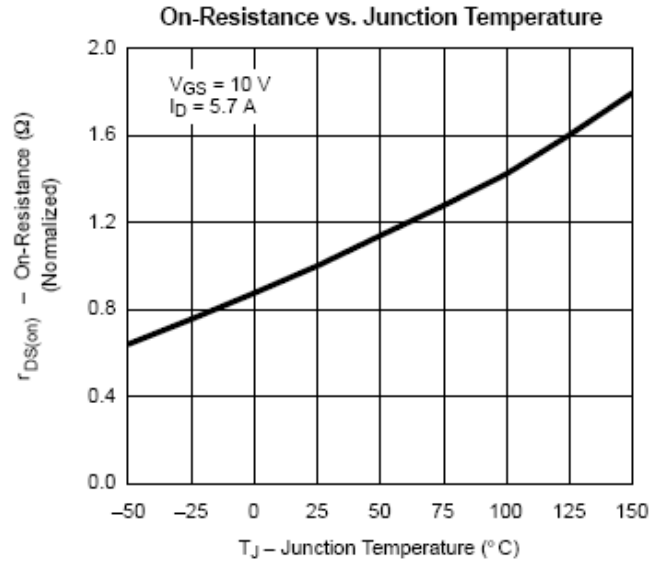
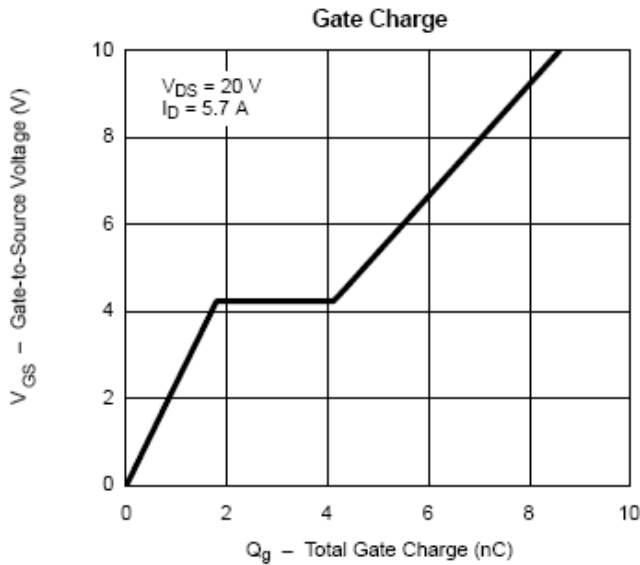




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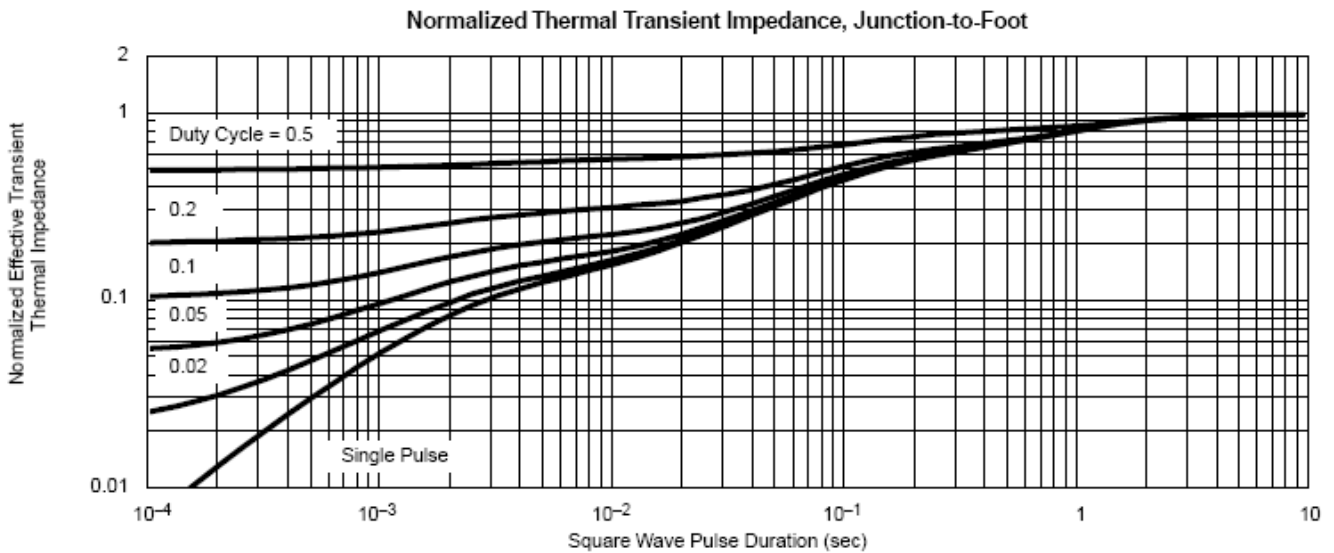
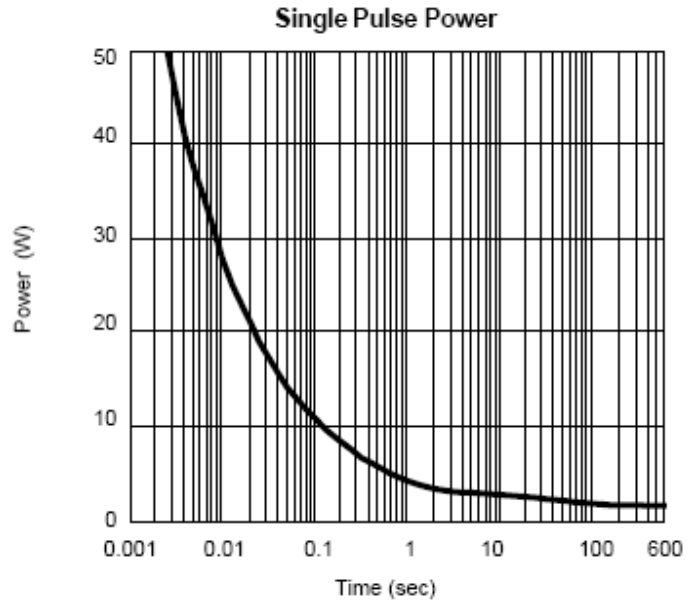
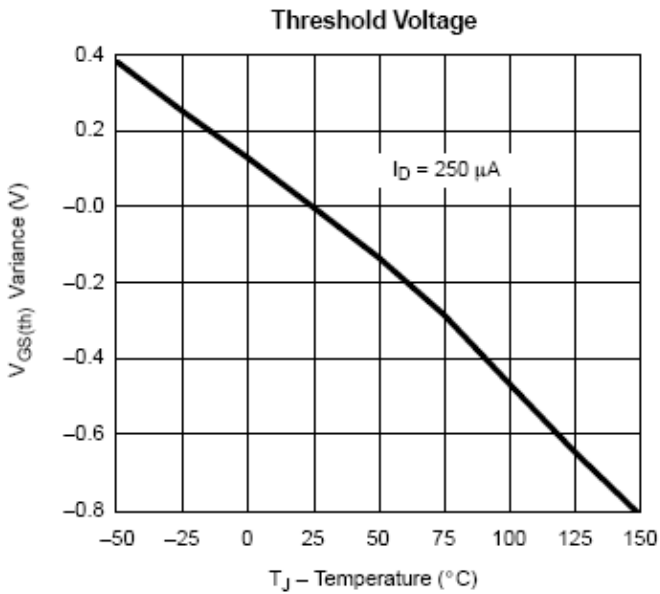
TYPICAL CHARACTERISTICS





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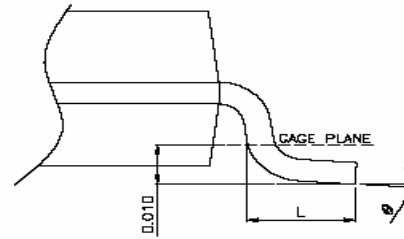
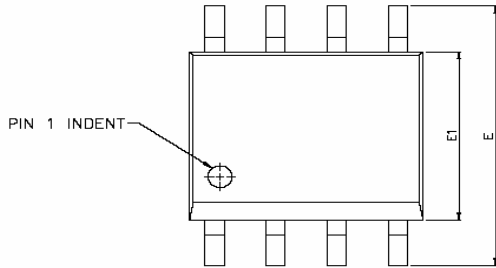
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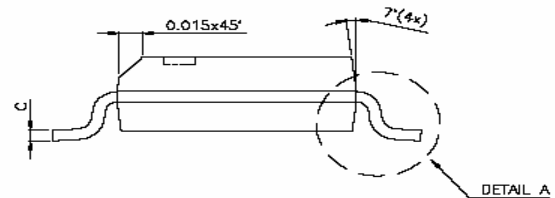
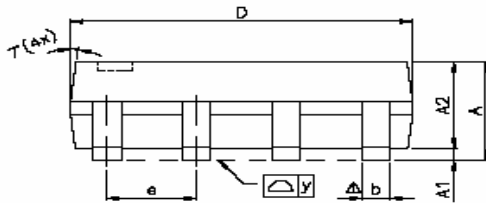


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SOP- 8 PACKAGE OUTLINE



DETAIL A



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.47	1.60	1.73	0.058	0.063	0.068
A1	0.10	—	0.25	0.004	—	0.010
A2	—	1.45	—	—	0.057	—
b	0.33	0.41	0.51	0.013	0.016	0.020
C	0.19	0.20	0.25	0.0075	0.008	0.0098
D	4.80	4.85	4.95	0.189	0.191	0.195
E	5.80	6.00	6.20	0.228	0.236	0.244
E1	3.80	3.90	4.00	0.150	0.154	0.157
e	—	1.27	—	—	0.050	—
L	0.38	0.71	1.27	0.015	0.028	0.050
Δ y	—	—	0.076	—	—	0.003
θ	0°	—	8°	0°	—	8°



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